

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

YOR9-2000-0174

Application Number

09/612,260

Applicant(s)

Cohen et al

Filing Date

July 7, 2000

Group Art Unit

2811

U.S. PATENT DOCUMENTS

| *EXAMINER INITIAL | REF | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
|----------------------|-----|-----------------|----------|-------------------|-------|----------|-------------------------------|
| DH/L | | 5,102,819 | 04/07/92 | Matsushita et al. | | | |
| DH/L | | 5,273,921 | 12/28/93 | Neudeck et al. | | | |
| DH/L | | 6,143,582 | 11/07/00 | Vu et al. | | | |
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FOREIGN PATENT DOCUMENTS

| | REF | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | Translation | |
|--|-----|-----------------|------|---------|-------|----------|-------------|----|
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

| | | |
|------|--|---|
| DH/L | | Wong, et al., "SELF-ALIGNED (TOP AND BOTTOM) DOUBLE-GATE MOSFET WITH A 25 nm THICK SILICON CHANNEL", Electron Devices Meeting, 1997, Technical Digest, International, 1997, pp. 427-430 |
| DH/L | | Lee et al., "SUPER SELF-ALIGNED DOUBLE-GATE (SSDG) MOSFETs UTILIZING OXIDATION RATE DIFFERENCE AND SELECTIVE EPITAXY", IEDM, December 5, 1999, IEEE, 1999 |

EXAMINER

Donghee Kang

DATE CONSIDERED

8-10-01

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

YOTR9-2000-017

Application Number

09/612,260

Applicant(s)

Cohen et al.

Filing Date

July 7, 2000

Group Art Unit

2811

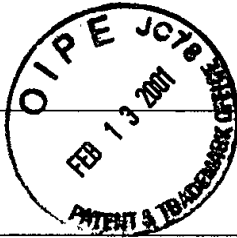
AMINER

INITIAL

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

DNH

Su et al., "NEW PLANAR SELF-ALIGNED DOUBLE-GATE FULLY-DEPLETED P-MOSFET's USING EPITAXIAL LATERAL OVERGROWTH (ELO) AND SELECTIVELY GROWN SOURCE/DRAIN (S/D), IEEE SOI Conference, October, 2000



EXAMINER

Donghee Kang

DATE CONSIDERED

8-16-01

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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| Docket Number (Optional) YOR9-2000-0114 | Application Number 09/612,260 |
| Applicant(s) Cohen et al. | |
| Filing Date July 7, 2000 | Group Art Unit 2811 |

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Donghee Kang

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